

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
60V	5Ω @ $V_{GS} = 10\text{V}$	115mA

## Description and Applications

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Load switches
- Power management functions
- Motor controls
- PWM applications

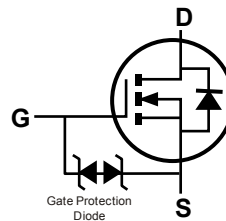


ESD PROTECTED, 1KV

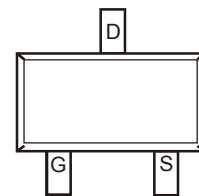
SOT523



Top View



Equivalent Circuit



Top View  
Pin Out

## Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.**

<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

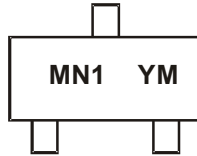
- Case: SOT523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208 ③
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Weight: 0.002 grams (approximate)

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN66D0LT-7	SOT523	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



MN1 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or Y= Year ex: I = 2021  
 M = Month ex: 9 = September

### Date Code Key

Year	2008	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V	.....	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	60	V
Gate-Source Voltage	Continuous	±20	V
Drain Current (Note 5)	Continuous	115	mA
	Continuous @ +100°C	73	
	Pulsed	800	

## Thermal Characteristics (@ T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics (@ T<sub>A</sub> = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	70	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0 500	μA	@ T <sub>C</sub> = +25°C @ T <sub>C</sub> = +125°C V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±5	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.2	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	3.5 3.0	6 5	Ω	@ T <sub>C</sub> = +25°C @ T <sub>C</sub> = +125°C V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 0.115A V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	23	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	3.4	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	1.4	—	pF	
<b>SWITCHING CHARACTERISTICS (Note 7)</b>						
Turn-On Delay Time	t <sub>D(on)</sub>	—	10	—	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.115A, R <sub>L</sub> = 150Ω, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-Off Delay Time	t <sub>D(off)</sub>	—	33	—	ns	

Notes:  
 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.  
 6. Short duration pulse test used to minimize self-heating effect.  
 7. Guaranteed by design. Not subject to product testing.

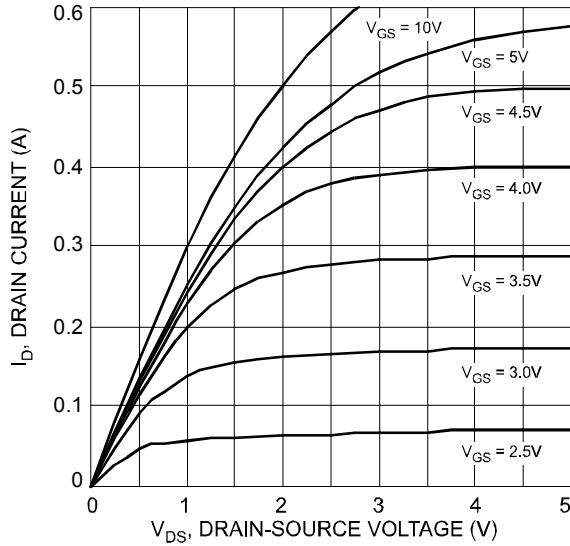


Fig. 1 Typical Output Characteristic

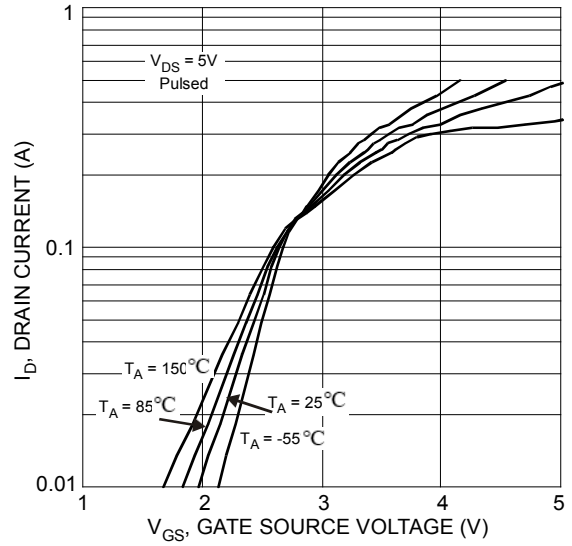


Fig. 2 Typical Transfer Characteristics

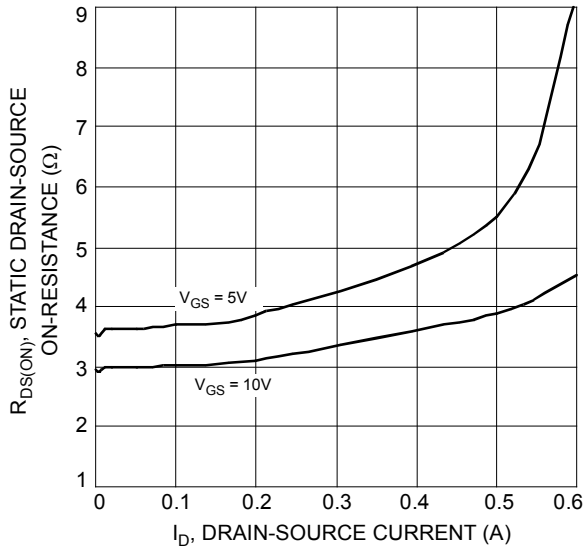


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

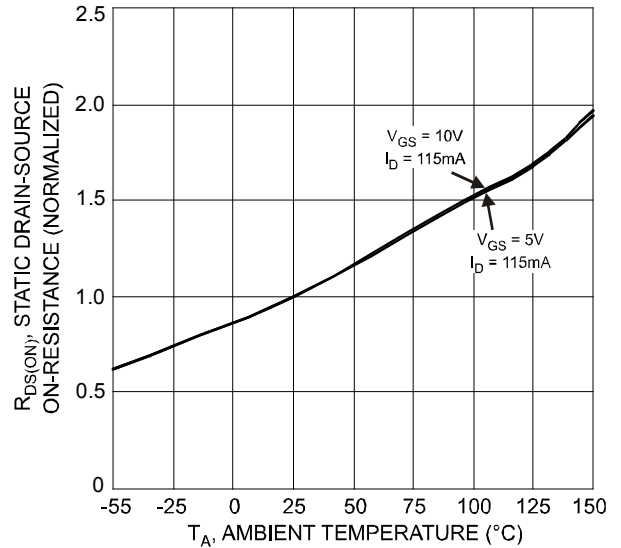


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

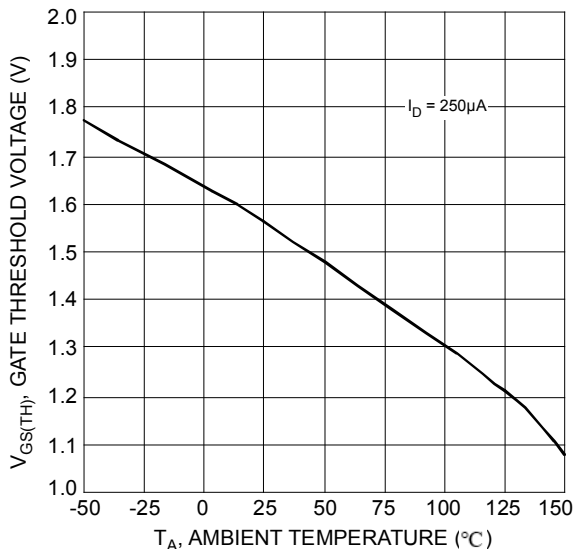


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

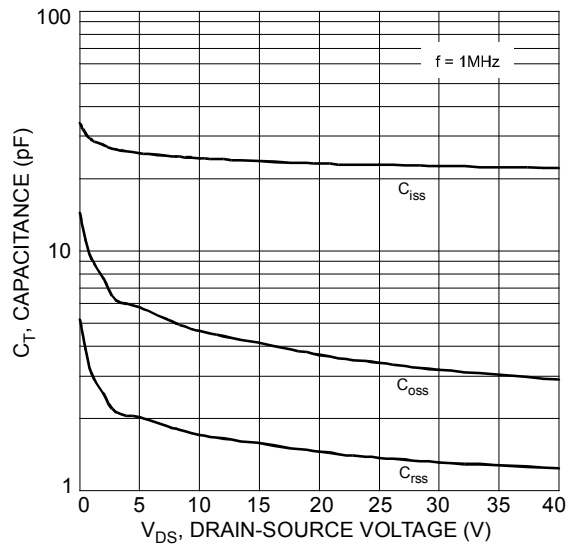


Fig. 6 Typical Total Capacitance

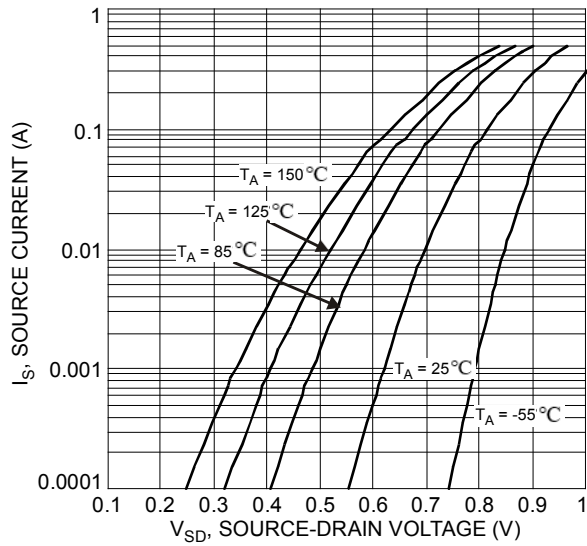
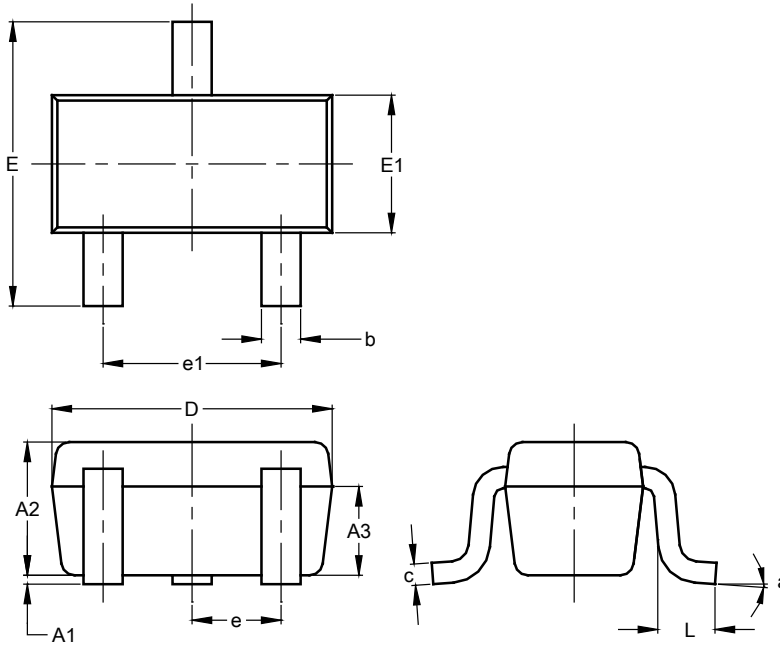


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**

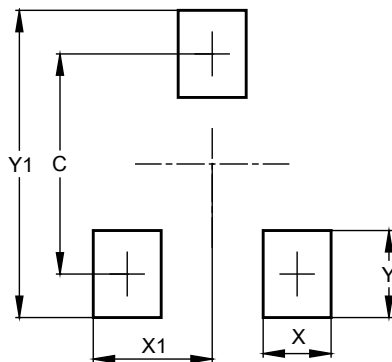


SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT523**



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80

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